

UTILITY PATENT APPLICATION TRANSMITTAL LETTER

(Only for new nonprovisional applications under 37 CFR 1.53(b))

Docket No.
NE063**To the Assistant Commissioner for Patents:**

Transmitted herewith for filing is the patent application of:

Nobuyuki Ishiwata, Hisanao Tsuge, Hisao Matsutera, Yuji Tsukamoto, Masafumi Nakada & Atsushi Kamijo corresponding to Japanese application No. 9-335501, filed December 5, 1997, entitled: MAGNETO-RESISTANCE EFFECT TYPE COMPOSITE HEAD AND PRODUCTION METHOD THEREOF.

Enclosed are:

<input checked="" type="checkbox"/>	41 pages of specification.
<input checked="" type="checkbox"/>	12 sheets of formal drawings.
<input checked="" type="checkbox"/>	a newly-executed declaration of the inventors.
<input type="checkbox"/>	a copy of an executed declaration of the inventor from prior application Serial No. , filed .
<input type="checkbox"/>	incorporation by reference. The entire disclosure of the prior application, from which a copy of the oath or declaration is supplied as indicated in the preceding box, is considered as being part of the disclosure of the accompanying application and is hereby incorporated by reference therein.
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Docket No.
NE063

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TOTAL CLAIMS	20 - 20 =	0	x\$ 18	
INDEPENDENT CLAIMS	2 - 3 =	0	x\$ 78	
MULTIPLE DEPENDENT CLAIM PRESENT			\$ 260	

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December 3, 1998

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[illegible]

Magneto-resistance Effect Type Composite Head and
Production Method Thereof

BACKGROUND OF THE INVENTION

1. Field of the Invention

5 The present invention relates to a thin film
magnetic head used in a magnetic disc apparatus and in
particular, to a magnetic recording/reproduction head
using the magneto-resistance effect obtained by
ferromagnetic tunnel junction.

10 2. Description of Related Arts

As the magnetic recording apparatus reduces its size
reduction and increases capacity, a magneto-resistance
effect type head (hereinafter, referred to as an MR head)
15 having a large reproduction output has been used in
practice. Such an MR head is already described in "A
Magneto-resistivity Readout Transducer", IEEE Trans. On
Magn., MAG7, 1971, page 150 [1].

In order to improve the conventional MR head, there
20 has been developed a GMR head using a giant magneto-
resistance effect (hereinafter, referred to as GMR)
capable of realizing a further increased reproduction
output. This GMR uses the magneto-resistance effect

called spin-valve effect in which a resistance change corresponds to a cosine of a magnetization direction of two adjacent magnetization layers. This enables to obtain a large resistance change with a small operation magnetic field. The MR head using the spin-valve effect is described in "Design, Fabrication & Testing of Spin-Valve Read Heads for High Density Recording", IEEE Trans. On Magn., Vol. 30, No. 6, 1994, page 3801 [2]. However, the magneto-resistance change ratio obtained by the spin-valve effect that can be applied to an actual MR head is only several percents. When reducing a track width for increasing the recording density, it is necessary to obtain a magneto-resistance effect having a greater resistance change ratio.

The ferromagnetic tunnel junction has a configuration including two ferromagnetic layers sandwiching a tunnel barrier layer made from a thin insulator body having a thickness of several nanometers. In this configuration, when a constant current flows between the ferromagnetic layers while an external magnetic field is applied into the ferromagnetic layers, a magneto-resistance effect phenomenon can be seen. That is, a resistance value is changed according to a relative angle of magnetization directions of the two magnetic layers. This is called a ferromagnetic tunnel junction magneto-resistance effect (TMR). The resistance value is minimum when the magnetization directions are parallel to

each other, and maximum when the magnetization directions are anti-parallel to each other. That is, the parallel and the anti-parallel states can be obtained depending on the intensity of the magnetic field. Accordingly, it is possible to detect a magnetic field according to a change of the resistance value.

Recently, there has been developed a TMR element exhibiting a magneto-resistance change ratio near to 20% by forming an Al oxide surface film on the tunnel barrier layer. This increases the possibility to apply the TMR element to a magnetic head and a magnetic memory. An example of such a large magneto-resistance change ratio is described in "Journal of Applied Physics", Vol. 79, 1996, page 4724 to 4729 [3].

That is, using a deposition mask, a first ferromagnetic layer of CoFe is formed on a glass substrate by way of vacuum deposition. Subsequently, the deposition mask is exchanged, and an Al layer is formed to have a thickness of 1.2 to 2.0 nm. This Al surface is subjected to an oxygen glow discharge so as to form a tunnel barrier layer of Al_2O_3 . After this, a second ferromagnetic layer of Co is formed on this tunnel barrier layer over the first ferromagnetic layer, thus completing a cross electrode type ferromagnetic tunnel element. This method enables to obtain a magneto-resistance change ratio as large as 18%.

Various TMR elements are disclosed in Japanese Patent Publication (Unexamined) No. A-5-63254 [4], Japanese Patent Publication (Unexamined) No. A-6-244477 [5], Japanese Patent Publication (Unexamined) No. A-8-70148 [6], Japanese Patent Publication (Unexamined) No. A-8-70149 [7], Japanese Patent Publication (Unexamined) No. A-8-316548 [8], and "1997 Journal of Japan Applied Magnetism Society, vol. 21, pp. 493 to 496 [9]. These documents give a description on a method in which the Al layer formed is exposed to the atmosphere for epitaxy of Al_2O_3 .

When applying the TMR element to a device such as a magnetic head and memory, it is necessary to reduce affects from a thermal noise. In this case, it is necessary to have a sufficiently low resistance value in practical element dimensions. However, in the conventional tunnel barrier formation method, it is difficult to realize this. Moreover, in application to a magnetic head of high-density design, the signal output voltage becomes a key point. However, with the conventional technique, it is impossible to obtain a sufficiently high density without deteriorating the element characteristic. Furthermore, with the conventional technique, there has been a problem that characteristic fluctuations among elements in a wafer or between lots are too great to obtain a sufficient yield for practical use.

The aforementioned problems are considered to come from the conventional tunnel barrier layer formation method. In the method using the oxygen glow discharge, active oxygen in the radical state or ion is used for oxidation of the conductive layer and accordingly, it is difficult to control the thickness of the oxide film, i.e., element resistance. Moreover, there is a problem that the tunnel barrier layer is contaminated with activated impurities gas generated simultaneously. On the other hand, the method using natural oxidation in the atmosphere also have various problems. For example, a pin hole may be generated in the tunnel barrier layer by dusts in the atmosphere, and the tunnel barrier layer is contaminated with humidity, carbon oxide, or nitrogen oxide, similarly in the oxygen glow discharge method.

Japanese Patent Application No. 9-209292 [10] discloses a TMR element production method having a practically sufficient resistance value and signal output voltage characteristic with an improved yield. This method includes: a step for successively forming a first ferromagnetic layer, a tunnel barrier layer, and a second ferromagnetic layer; a step for forming a conductive layer of a metal or semiconductor; and a step for introducing oxygen into vacuum for natural oxidation of a surface of this conductive layer so as to form a tunnel barrier layer.

Furthermore, Document [10] discloses a TMR element production method for successively forming a first ferromagnetic layer, a tunnel barrier layer, and a second ferromagnetic layer while maintaining a vacuum. After
5 the first ferromagnetic layer is formed, an oxygen is introduced to oxidize a surface of the first ferromagnetic layer while maintaining the vacuum, and after formation of a conductive layer of metal or semiconductor, an oxygen is introduced into the vacuum
10 for natural oxidization of a surface of this conductive layer to form the tunnel barrier layer.

With reference to Fig. 11, explanation will be given on the TMR film production method disclosed in Document [10]. Firstly, an undercoat layer 10, a first
15 ferromagnetic layer 11, and a conductive layer 12 are successively formed in a vacuum (Fig. 11A). A pure oxygen is introduced without breaking the vacuum, for natural oxidation of a surface of the conductive layer 12 to form a tunnel barrier layer 13 (Fig. 11B). It should
20 be noted that Fig. 11B shows that even after the oxidation of the conductive layer, there is left an un-oxidized portion on the boundary with the first ferromagnetic layer 11. It is also possible to completely oxidize the conductive layer by setting the
25 oxidation conditions as such. After exhausting the oxygen, the second ferromagnetic layer 14 is formed to complete the basic configuration of the TMR film (Fig.

11C). Next, an antiferromagnetic layer 15 is formed to complete the basic configuration of the TMR element (Fig. 11D).

In the aforementioned method, it is possible to obtain an epitaxy of an oxide layer while maintaining a thermal equilibrium in a clean atmosphere not affected by a gas from impurities, thus enabling to control to form a high-quality tunnel barrier layer. Moreover, by controlling the oxygen pressure and the substrate temperature, it is possible to obtain an element of a low resistance and a high current density required for application to a device such as a magnetic head. Furthermore, it is possible to obtain a uniform element characteristic within a wafer and stable repeatability between lots. When the ferromagnetic layer contains Fe, Co, Ni or an alloy containing them and if the conductive layer is made from an Al material having a surface free energy smaller than that of the ferromagnetic layer, it is possible to obtain a preferable coating with respect to the first ferromagnetic layer serving as an undercoat layer. As a result, in an element completed, it is possible to obtain a preferable characteristic having no electrical short-circuit between the ferromagnetic layers due to a pin hole. Moreover, the free energy required for oxidation of Al per one oxygen atom is greater than Fe, Co, Ni, and accordingly, the Al_2O_3 serving as the tunnel barrier is thermally stabilized on the junction

boundary. When Mg or a metal of lanthanoid is selected for the conductive layer, it is possible, from the same reason, to obtain a preferable coating characteristic with respect to the first ferromagnetic layer serving as the undercoat as well as to obtain a thermally stable tunnel barrier.

Referring to Fig. 12, explanation will be given on the conventional TMR element production method disclosed in Document [10]. After formation of the first ferromagnetic layer 11 (Fig. 12A), oxygen is introduced into the vacuum for forming an oxide layer 21 on the surface of the first ferromagnetic layer 11 (Fig. 12B). When forming the conductive layer 12 in the next step, oxygen is diffused from the first ferromagnetic layer 11 into the conductive layer 12 (Fig. 12C), and an oxide layer 23 is also formed at the side of the conductive layer 12. In this method, the oxide layer 24 of the conductive layer 12 is formed on both boundaries in contact with the ferromagnetic layers, enabling to exhibit an excellent thermal stability. After exhausting the oxygen, the second ferromagnetic layer 14 is formed (Fig. 12 E) and the antiferromagnetic layer 15 is formed to complete the basic configuration of the TMR element (Fig. 12F). In order to form a stable oxide layer at the side of the conductive layer 12, the conductive layer 12 should have a greater free energy for oxidization per one oxygen atom than an element constituting the

ferromagnetic layer 11. When the ferromagnetic layer contains Fe, Co, Ni, or an alloy containing them, it is effective that the conductive layer 12 uses Al, Mg, or a metal belonging to lanthanoid.

5 Fig. 10 shows a configuration example of an air bearing surface (ABS) of a magnetic head using the conventional TMR element which is described in "Nikkei Electronics", No. 686, April 7, 1997 [11]. The TMR element including a TMR film having electrodes formed at
10 its ends is contained through an insulation film in a magnetic shield.

In the apparatus having the configuration shown in Fig. 10, the TMR element 119 including an insulation film 117, a TMR film, and upper and lower electrode films 118
15 is present between the magnetic shields which determine the resolution of a reproduction head. Accordingly, it is possible to reduce the distance between the shields while maintaining a sufficient insulation between the TMR element and the upper and lower magnetic shields.

20 However, it is difficult to prepare a thin insulation film and it is impossible to reduce the distance between the magnetic shields smaller than the thickness of the TMR element. Furthermore, for reducing the track width, the electrodes (right and left) need be patterned on the
25 top and bottom of the TMR film so as to make the distance between the electrodes in the order of submicrons, which

is quite difficult in the process using a photo-resist. Furthermore, to cope with a noise increase caused by reduction in size of the TMR element, it is necessary to apply a certain bias magnetic field.

5

SUMMARY OF THE INVENTION

It is therefore an object of the present invention to provide a recording/reproduction head using a TMR element for a high-density recording and reproduction that enables to realize a high resolution for a high line density and to reduce a track width for a high track density, and a production method thereof.

The magneto-resistance effect type composite head according to the present invention comprises: a first magnetic shield and a second magnetic shield successively layered on a slider; a reproduction head including a magneto-resistance effect element (hereinafter, referred to as an MR element) arranged between the first and the second magnetic shields; and a recording head arranged adjacent to the reproduction head so as to use the second magnetic shield as a first magnetic pole film and having a second magnetic pole film opposing to the first magnetic pole via a magnetic gap;

the MR element comprising:
a center region including a ferromagnetic tunnel junction magneto-resistance effect film (hereinafter,

forming step, there is a step for forming an insulation film arranged to cover the TMR element and patterned to determine a reproduction track width in the center region.

5

BRIEF DESCRIPTION OF THE DRAWINGS

Fig. 1 shows a layered configuration of a magneto-resistance effect (MR) composite head according to a first embodiment of the present invention.

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Fig. 2 shows a layered configuration of a magneto-resistance effect (MR) composite head according to a second embodiment of the present invention.

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Fig. 3 shows a layered configuration of a magneto-resistance effect (MR) composite head according to a third embodiment of the present invention.

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Fig. 4 shows a production procedure of the magneto-resistance effect (MR) composite head according to the first embodiment of the present invention, including steps of forming a lower shield (A); undercoat/TMR film (B); TMR patterning (insulation/PM/non-magnetic insulation film formation) (C); element patterning (leaving the insulation film) (D); resist pattern formation for insulation film lift-off (E); an insulation

film lift-off (F); forming a hole in the insulation film (G); and a shield formation (H).

Fig. 5 shows a layered configuration of a magneto-resistance effect (MR) composite head according to a fifth embodiment of the present invention.

Fig. 6 shows a layered configuration of a magneto-resistance effect (MR) composite head according to a sixth embodiment of the present invention.

Fig. 7 shows a production procedure of a layered configuration of a magneto-resistance effect (MR) composite head according to a seventh embodiment of the present invention, including steps of forming a lower shield (A); undercoat/TMR film (B); TMR patterning (insulation/PM/non-magnetic insulation film formation) (C); element patterning (leaving the insulation film) (D); forming a hole in the insulation film (G); and a shield formation (H).

Fig. 8 shows a magneto-resistance effect (MR) composite head production procedure according to an embodiment of the present invention.

Fig. 9 shows a magneto-resistance effect (MR) composite head production procedure according to another embodiment of the present invention.

Fig. 10 shows a layered configuration of an MR composite head using a conventional ferromagnetic tunneling element.

Fig. 11 shows a production procedure of a conventional MR composite head using a conventional ferromagnetic tunneling film.

Fig. 12 shows a production procedure of a conventional MR composite head using a conventional ferromagnetic tunneling film.

DESCRIPTION OF THE PREFERRED EMBODIMENTS

Description will now be directed to embodiments of the present invention with reference to the attached drawings.

[Embodiment 1]

Fig. 1 shows a layered configuration of a magneto-resistance effect type composite head according to a first embodiment of the present invention viewed from a surface (air baring surface, hereinafter referred to as an ABS surface) opposing to a medium. This head includes a head for a reproduction function made from two magnetic shields 101 and 111 successively layered on a slider, and a TMR element provided between the two magnetic shields 101 and 111. Furthermore, the head includes a head for a recording function. One of the magnetic shields, i.e.,

111 also serves as one magnetic pole film 111. On this magnetic pole film 111, i.e., on the side not having the magneto-resistance effect element, there are successively layered a coil sandwiched by insulation bodies and
5 another magnetic pole 113. A magnetic gap 112 is provided between the magnetic poles 111 and 113. A magnetic field generated in this magnetic gap 112 enables to perform recording.

The aforementioned composite head is prepared as follows. Firstly, from the side of the lower shield 101,
10 a Ta film 102 with a thickness of 30 nm, a first ferromagnetic layer 103 made from a Ni-Fe film with a thickness of 10 nm, and a conductive layer of Al film with a thickness of 10 nm were successively formed in
15 this order by way of sputter deposition. After this, a surface of the Al conductive layer was oxidized to form a tunnel barrier layer 104. Next, a second ferromagnetic layer 105 of Co-Fe film and an antiferromagnetic film 106 of Ni-Mn film with a thickness of 20 nm were formed by
20 way of sputter deposition, thus completing a TMR film. After formation of the TMR film, sputter deposition was carried out to form a non-magnetic insulation layer 107 made from alumina, a permanent magnet layer 108 made from CoCrPt, and a non-magnetic layer 109 made from Ta. With
25 this configuration, the end surface of the TMR film patterned is coated by the non-magnetic layer before formation of the permanent magnet layer. Accordingly,

there was no danger of electrical short-circuit between the two magnetic layers facing to each other via the tunnel barrier layer of the TMR film, thus enabling to maintain a preferable TMR characteristic. Furthermore, 5 the insulation layer 110 was formed by way of sputter deposition and the upper shield 111 was formed as a Ni-Fe film with a thickness of 3 micrometers by way of frame plating. The magnetic gap 112 was formed using alumina. Subsequently, a Cu coil was formed by way of the frame 10 plating method. Furthermore, the upper magnetic pole 113 for the recording function was formed as a Ni-Fe film with a thickness of 4 micrometers by way of the frame plating method.

A TMR element includes a center region made from a 15 ferromagnetic TMR film and an end region layered so as to sandwich this center region from right and left. The center region has the tunnel barrier layer sandwiched between the first and the second ferromagnetic layers for generating a magneto-resistance effect with a current 20 flowing almost in a vertical direction between the magnetic shields 101 and 111 serving as electrodes.

The aforementioned configuration enables to apply a bias magnetic field to the TMR element. This enables to realize a high resolution and a high track density with a 25 reduced track width.

Hereinafter, description will be directed to a production procedure of the head according to the first

embodiment. A wafer substrate constituting a slider is made from a composite ceramic of Al_2O_3 -TiC. On this wafer substrate, a CoTaZr film was formed with a thickness of 1 micrometer by way of the sputtering and patterned as the lower shield 101. During formation of this CoTaZr film, a uni-directional magnetic field was applied in a horizontal direction in Fig. 1. After this, a uni-directional magnetic field of 500 Oe was applied to this magnetic anisotropic direction while an initial thermal treatment was carried out at a temperature of 350 degrees C for 1 hour.

Next, the TMR film to become the center region was formed by way of the sputtering method as follows. Firstly, from the side of the lower shield (101), the Ta film (102) with thickness of 30 nm, the first ferromagnetic layer (103) with a thickness of 10 nm, and a conductive layer of Al film with a thickness of 2 nm were successively formed in this order by way of the sputter deposition. This film formation was carried out by using a high frequency magnetron sputter apparatus having four 4-inch targets. The sputter condition was set to a background pressure of 1×10^{-7} Torr or below, Ar pressure of 10 mTorr, and a high frequency power of 200 W. Next, a pure oxygen was introduced into the sputter apparatus with an oxygen pressure maintained in a range of 20 mTorr to 200 Torr for 10 minutes for oxidizing the surface of the Al conductive layer so as to form the

tunnel barrier layer (104). After the oxygen was exhausted to reach the background pressure, the sputter deposition was employed to form the second ferromagnetic layer (105) made from a Co-Fe film with a thickness of 20 nm and an antiferromagnetic layer made from a Ni-Mn film with a thickness of 20 nm, thus completing the TMR film.

After this, in order to generate an exchange interaction magnetic field between the second ferromagnetic layer 105 and the antiferromagnetic layer 106 so as to fix the magnetization of the second ferromagnetic layer 105 in a direction vertical to the ABS surface in Fig. 1, a uni-directional magnetic field of 30 kOe was applied in vertical direction to the ABS surface while carrying out a thermal treatment at 270 degrees C for 5 hours. This magnetic field had a direction vertically intersecting the direction of the magnetic field applied when the lower shield was subjected to the thermal treatment. The lower shield of CoTaZr film had been thermally treated at 350 degrees C and its axis of easy magnetization would not be changed by the thermal treatment this time and maintained the anisotropic magnetic field H_k of 80e, sufficient for a magnetic shield. Next, patterning of the TMR film was carried out to form the center region, which was followed by formation of the end region.

[Embodiment 2]

Fig. 2 shows a layered configuration of a magneto-resistance effect type composite head according to a second embodiment of the present invention viewed from the ABS surface opposing to a medium. The TMR film is constituted by an undercoat layer 102, an antiferromagnetic layer 106, a first ferromagnetic layer 105, a tunnel barrier layer 104, a second ferromagnetic layer 103, and a non-magnetic conductive layer 114. The TMR film according to the second embodiment has a configuration different from that of the first embodiment. The TMR film according to the second embodiment was constituted by following layers successively formed in this order from the side of the lower shield 101, employing a continuous sputter deposition: a Ta film 102 with a thickness of 30 nm, an antiferromagnetic layer 106 of Pt-Mn film with a thickness of 20nm; a first magnetic layer 105 made from a Co film with a thickness of 20 nm; and a conductive layer of Al film with a thickness of 2 nm. The Al conductive layer constituting the tunnel barrier layer 104 was formed using the sputter apparatus used in Embodiment 1 with the same sputtering conditions as in Embodiment 1. Oxygen was exhausted to reach the background pressure before successively forming by way of sputter deposition a second ferromagnetic layer 103 of a Ni-Fe-Co film with a thickness of 10 nm and a non-magnetic conductive layer 114 of Ta film with a thickness of 30 nm, thus completing

the TMR film. After this, magnetization of the second ferromagnetic layer 114 was fixed in the vertical direction to the ABS surface using the same procedure and conditions as in Embodiment 1. Thus, the second
5 embodiment is identical to the first embodiment except for the configuration of the TMR film and can exhibit the same effect as the first embodiment.

[Embodiment 3]

10 Fig. 3 shows a layered configuration of a magneto-resistance effect type composite head according to a third embodiment of the present invention viewed from the ABS surface opposing to a medium. The TMR film is constituted by an undercoat layer 102, a first
15 ferromagnetic layer 103, a tunnel barrier layer 104, a second ferromagnetic layer 105, and an antiferromagnetic layer 106. The third embodiment differs from the first embodiment in that the junction between the TMR film and the upper shield 111 is not exposed to the ABS surface.

20 This can be obtained by designing the mask which determines the track width of the TMR film when carrying out the lift-off of the insulation film 110, in such a manner that the end face of the TMR film is arranged at a deeper position with respect to the ABS surface. The
25 distance between the TMR end face to the ABS surface was set to a range from 0.1 to 1 micrometer. The third embodiment is identical to the first embodiment except

for the configuration of the TMR film and can exhibit the same effects as the first embodiment.

[Evaluation of Embodiments 1 to 3]

- 5 The TMR elements according to the first, the second, and the third embodiments were respectively cut off from the wafers and processed into a slider configuration for a magnetic disc, and then mounted on an arm having a gimbal spring for recording/reproduction evaluation.
- 10 Here, the permanent magnet was magnetized with a magnetic field of 3 kOe. The magneto-resistance change ratio actually obtained was about 15%. The magneto-resistance change ratio did not change at all up to 10^3 A/cm² while increasing the current density. At 5×10^3 A/cm², the
- 15 resistance value stayed almost unchanged and the magneto-resistance change ratio decreased only by about 10%. The signal output voltage of the TMR head according to the first and the second embodiment was about 1 mV with a current density of 10^3 A/cm² and about 3 mV with a current
- 20 density of 5×10^3 A/cm². The signal output voltage of the TMR head according to the third embodiment was about 2 mV with a current density of 5×10^3 A/cm². When used for a reproduction magnetic head, the TMR element according to the first embodiment can cope with a
- 25 recording density of 3 Gb/in² or above, and the TMR element according to the second embodiment can cope with a recording density of 30 Gb/in² or above. In the third

embodiment, the junction between the TMR film and the upper shield 111 is arranged at a deeper position with respect to the ABS surface. Accordingly, even when the ABS surface was in contact with a medium surface, no noise was caused by a heat dissipation due to a contact, enabling to obtain a stable operation without a noise.

[Embodiment 4]

Fig. 4 shows a production procedure of the TMR film of the aforementioned magneto-resistance effect type composite head according to the first embodiment. On a wafer substrate made from a composite ceramic of Al_2O_3 -TiC constituting a slider, a FeTaN film was formed by sputtering so as to have a thickness of 1 micrometer, which was patterned as the lower shield 101 (Fig. 4A) and subjected to a thermal treatment at a temperature of 500 degrees C in a vacuum for 1 hour. During this thermal treatment, a uni-directional magnetic field was applied in the horizontal direction in Fig. 4.

Next, a TMR film was formed to constitute the center region by sputtering (Fig. 4B). Firstly, the lower shield 101 was covered with a Ta film 102 with a thickness of 30 nm, a first ferromagnetic layer 103 made from a Ni-Fe film with a thickness of 10 nm, and a conductive layer of an Al film with a thickness of 2 nm successively formed by sputter deposition in this order. This film formation was carried out using a high-

frequency magnetron sputter apparatus having four 4-inch targets. The sputtering condition was set as follows: the background pressure 1×10^{-7} Torr or below, Ar pressure 10 mTorr, high frequency power 200 W. Next, pure oxygen was introduced into the sputter apparatus and the oxygen pressure was maintained in a range from 20 mTorr to 200 Torr for 10 minutes for oxidizing the surface of the Al conductive layer to form the tunnel barrier layer 104. After the oxygen was exhausted to reach the background pressure, a second ferromagnetic layer 105 of a Co-Fe film with a thickness of 20 nm and an antiferromagnetic film of Ni-Mn film with a thickness of 20 nm were formed by way of sputter deposition, thus completing the TMR film.

The TMR film was patterned to form the center region. After this, an insulation film, a permanent magnet film (PM), and a non-magnetic film were formed as an end region to sandwich the center region, and lift-off was carried out (Fig. 4C). An element constituted by the center region and the end region was patterned (Fig. 4D). The insulation film was subjected to lift-off so as to determine the track width of the TMR film (Fig. 4E and 4F).

Fig. 8 shows a patterning procedure carried out after the TMR film was layered. The TMR film was formed by the method shown in Fig. 4 (Fig. 8A); a photo-resist

mask 1102 was formed (Fig. 8B); and the patterning was carried out using an ion beam (Fig. 8C).

With this photo-resist mask left, sputter deposition was carried out to form a non-magnetic insulation layer 1104 of alumina, a permanent magnet layer 1105 of CoCrPt, and a non-magnetic layer 1106 of Ta (Fig. 8D), and then lift-off was carried out (Fig. 8E). According to this method, the end face of the TMR film patterned is covered with the non-magnetic insulation layer before the permanent magnet layer is formed. Accordingly, no electrical short-circuit is caused between the two magnetic layers facing to each other via the tunnel barrier layer of the TMR film, enabling to maintain a preferable TMR characteristic.

Furthermore, another photo-resist mask 1107 was formed having a width identical to or narrower than the photo-resist mask 1102 (Fig. 8F); an insulation layer 1108 was formed by sputtering (Fig. 8G); and lift-off was carried out (Fig. 8H). After this, a hole was formed through the insulation film to use a part of the lower shield as an electrode (Fig. 4G). Furthermore, an upper shield of Ni-Fe film was formed with a thickness of 3 micrometers by way of the frame plating method (Fig. 4H).

After this, a magnetic gap was formed from alumina, and a coil for generating a recording magnetic field was formed. This coil was sandwiched by a photo-resist from its top and bottom for insulation. Firstly, a photo-

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resist pattern serving as the lower insulator was formed on the alumina magnetic gap and thermally hardened at 260 degrees C for 1 hour. Next, the frame plating method was used to form a Cu coil, and a photo-resist pattern

5 serving as the upper insulator was formed. This photo-resist pattern was also thermally hardened at 260 degrees C for 1 hour. Furthermore, a Ni-Fe film with a thickness of 4 micrometers was formed by way of the frame plating method so as to constitute an upper magnetic pole of the
10 recording head. After formation of this upper magnetic pole, a magnetic field of 1 kOe was applied in the direction of the axis of easy magnetization of the magnetic shield, and a thermal treatment was carried out at 200 degrees C for 1 hour. This stabilized the
15 magnetic anisotropy of the upper magnetic pole. Next, an electrode pattern was formed for the reproduction block and the recording block before the entire element was protected by an alumina sputter film. After this, in order align the magnetization of the antiferromagnetic
20 layer and the adjacent ferromagnetic layer, a uni-directional magnetic field of 3 kOe was applied in the vertical direction to the ABS surface while thermal treatment was carried out at 250 degrees C for 1 hour.

Fig. 11 shows a conventional production method which
25 can also be used to form the TMR film of the magneto-resistance effect composite head according to the first embodiment. According to the present embodiment, an

undercoat layer 10 of Fig. 11 is formed from Ta, a first ferromagnetic layer 11 is formed from Ni-Fe, and a conductive layer 12 is formed from Al (Fig. 11A). Oxygen is introduced into a vacuum for natural oxidization of the surface of the conductive layer 12 so as to form a tunnel barrier 13 (Fig. 11B). Next, a second ferromagnetic layer 14 is formed from Co-Fe (Fig. 11C); and an antiferromagnetic layer 15 is formed from Ni-Mn (Fig. 11D), thus completing a TMR element. The other production steps and processing conditions are identical to the conventional production method. In the present embodiment, the oxidized layer can grow in a thermal equilibrium in a clean atmosphere not affected by impurities gas, enabling to form a high-quality tunnel barrier layer under control. Moreover, the oxygen pressure and the substrate temperature can be controlled so as to obtain an element having a necessary resistance value and a high current density. Furthermore, it is possible to obtain a uniform element characteristic in a wafer and between lots.

Fig. 12 shows another conventional production method which can also be employed to form the TMR film of the magneto-resistance effect composite head according to the first embodiment. The undercoat layer 10 of Fig. 12 is formed from Ta, and the first ferromagnetic layer 11 is formed from Ni-Fe (Fig. 12A). After this, oxygen is introduced into a vacuum to form an oxidized layer 21 on

the surface of the first ferromagnetic layer 11 (Fig. 12B). In the next step, the Al film 12 is formed as a conductive layer, during which oxygen is diffused from the first ferromagnetic layer 11 into the conductive layer 12, thus obtaining an oxidized layer 23 at the side of the conductive layer 12 (Fig. 12C). After formation of the conductive layer 12, the vacuum is maintained while pure oxygen is introduced, so that on the surface of the conductive layer 12 oxidized naturally, a tunnel barrier layer 24 is formed in combination with the layer oxidized by the oxygen diffusion from the rear side (Fig. 12D). In this method, the oxidized layer 24 of the conductive layer 12 is formed on the both boundaries with the ferromagnetic layer. This enables to obtain an element having a further thermally stable characteristic. After the oxygen is exhausted, the second ferromagnetic layer 14 is formed from Co-Fe (Fig. 12E), and the antiferromagnetic layer 15 is formed from Ni-Mn, thus completing the basic configuration of the MR element (Fig. 12F). The TMR film thus obtained exhibits characteristics similar to the TMR film obtained according to the fourth embodiment.

The elements thus obtained were cut off from the wafer and processed into a slider configuration for a magnetic disc and mounted on a arm having a gimbal spring for evaluation of recording/reproduction characteristics.

The elements exhibited similar results as those obtained by the first, the second, and the third embodiments.

[Embodiment 5]

Fig. 5 shows a layered configuration of a magneto-resistance effect composite head apparatus according to a fifth embodiment of the present invention viewed from the ABS surface. The magneto-resistance effect composite head apparatus according to the fifth embodiment differs from that of the first embodiment in that the insulation layer 110 is absent between the non-magnetic layer 109 and the upper shield serving also as electrode 111.

The aforementioned magneto-resistance effect composite head was prepared as follows. A wafer substrate constituting a slider is made from a composite ceramic of Al_2O_3 -TiC. On this wafer substrate, a CoMoZr film was formed with a thickness of 1 micrometer by way of the sputtering and patterned as the lower shield 101. During formation of this CoMoZr film, a uni-directional magnetic field was applied in a horizontal direction in Fig. 5. After this, a uni-directional magnetic field of 500 Oe was applied to this magnetic anisotropic direction while an initial thermal treatment was carried out at a temperature of 350 degrees C for 1 hour.

Next, the TMR film to become the center region was formed by way of the sputtering method as follows. Firstly, from the side of the lower shield (101), the Ta

film (102) with thickness of 30 nm, the first ferromagnetic layer (103) with a thickness of 10 nm, and a conductive layer of Al film with a thickness of 2 nm were successively formed in this order by way of the sputter deposition. This film formation was carried out by using a high frequency magnetron sputter apparatus having four 4-inch targets. The sputter condition was set to a background pressure of 1×10^{-7} Torr or below, Ar pressure of 10 mTorr, and a high frequency power of 200 W. Next, a pure oxygen was introduced into the sputter apparatus with an oxygen pressure maintained in a range of 20 mTorr to 200 Torr for 10 minutes for oxidizing the surface of the Al conductive layer so as to form the tunnel barrier layer (104). After the oxygen was exhausted to reach the background pressure, the sputter deposition was employed to form the second ferromagnetic layer (105) made from a Co-Fe film with a thickness of 20 nm and an antiferromagnetic layer 106 made from a Ni-Mn film with a thickness of 20 nm, thus completing the TMR film.

After this, in order to generate an exchange interaction magnetic field between the second ferromagnetic layer 105 and the antiferromagnetic layer 106 so as to fix the magnetization of the second ferromagnetic layer 105 in a direction vertical to the ABS surface in Fig. 5, a uni-directional magnetic field of 30 kOe was applied in vertical direction to the ABS

surface while carrying out a thermal treatment at 270 degrees C for 5 hours. This magnetic field had a direction vertically intersecting the direction of the magnetic field applied when the lower shield was subjected to the thermal treatment. The lower shield of CoMoZr film had been thermally treated at 350 degrees C and its axis of easy magnetization would not be changed by the thermal treatment this time and maintained the anisotropic magnetic field H_k of 80e, sufficient for a magnetic shield. Next, patterning of the TMR film was carried out to form the center region, which was followed by formation of the end region as follows. A non-magnetic insulation layer 107 of alumina, a permanent magnet layer 109 of CoCrPt, and a non-magnetic layer 109 of Ta were formed by way of sputter deposition. According to this method, the end face of the TMR film patterned was coated with the non-magnetic layer before formation of the permanent magnet layer. Accordingly, there was no danger of an electrical short-circuit between the two magnetic layers facing to each other via the tunnel barrier layer of the TMR film, enabling to maintain a preferable TMR characteristic.

Referring to Fig. 5, the subsequent procedure will be explained. Using the frame plating method, a Ni-Fe film with a thickness of 3 micrometers was formed to constitute the upper shield 111, and a magnetic gap 112

was formed from alumina. After this, a coil for generating a recording magnetic field was formed.

This coil was sandwiched by a photo-resist from the top and bottom as follows. Firstly, on the aforementioned alumina magnetic gap, a photo-resist pattern was formed to constitute the lower insulator and thermally hardened at a temperature of 260 degrees C for 1 hour. Next, the frame plating method was used to form a Cu coil, and a photo-resist pattern constituting the upper insulator was formed, which was thermally hardened at a temperature of 260 degrees C for 1 hour.

Next, a Ni-Fe film with a thickness of 4 micrometers was formed by way of the frame plating method so as to constitute the upper magnetic pole 113 of the recording head. After formation of the upper magnetic pole, a magnetic field of 1 kOe was applied in the direction of the axis of easy magnetization of the magnetic shield and thermal treatment was carried out at a temperature of 200 degrees C for 1 hour. This stabilized the magnetic anisotropy of the upper magnetic pole. After formation of the electrode pattern for the reproduction block and the recording block, the entire element was protected by an alumina sputter film. After this, in order to align magnetization of the antiferromagnetic layer 106 and the adjacent ferromagnetic layer 105, a uni-directional magnetic field of 3 kOe was applied in the vertical

direction to the ABS surface while thermal treatment was carried out at a temperature of 250 degrees C for 1 hour.

[Embodiment 6]

5 Fig. 6 shows a layered configuration of a magneto-resistance effect composite head according to a sixth embodiment of the present invention viewed from the ABS surface. The magneto-resistance effect composite head according to the sixth embodiment is identical to that of

10 the second embodiment except for that the insulation layer 110 is absent between the non-magnetic layer 109 and the upper shield 111 serving also as the electrode 111. That is, the TMR film according to the sixth embodiment was constituted by following layers

15 successively formed in this order from the side of the lower shield 101, by way of a continuous sputter deposition: a Ta film 102 with a thickness of 30 nm, an antiferromagnetic layer 106 of Pt-Mn film with a thickness of 20nm; a first magnetic layer 105 made from a

20 Co film with a thickness of 20 nm; and a conductive layer of Al film with a thickness of 2 nm. The same sputter apparatus used in embodiment 5 was used for oxidization of the Al conductive layer to form the tunnel barrier layer 104 with the same sputtering conditions as in

25 Embodiment 1. Oxygen was exhausted to reach the background pressure before successively forming by way of sputter deposition a first ferromagnetic layer 103 of a

Ni-Fe-Co film with a thickness of 10 nm and a non-magnetic conductive layer 114 of Ta film with a thickness of 30 nm, thus completing the TMR film. After this, in order to generate an exchange interaction magnetic field between the second ferromagnetic layer 105 and the antiferromagnetic layer 106 so as to fix the magnetization of the second ferromagnetic layer 105 in a direction vertical to the ABS surface in Fig. 1, a unidirectional magnetic field of 30 kOe was applied in vertical direction to the ABS surface while carrying out a thermal treatment at 270 degrees C for 5 hours. This magnetic field had a direction vertically intersecting the direction of the magnetic field applied when the lower shield was subjected to the thermal treatment.

[Evaluation of Embodiments 5 and 6]

The TMR elements according to the fifth and the sixth embodiments were respectively cut off from the wafers and processed into a slider configuration for a magnetic disc, and then mounted on an arm having a gimbal spring for recording/reproduction evaluation. Here, the permanent magnet was magnetized with a magnetic field of 3 kOe. The magneto-resistance change ratio actually obtained was about 15%. The magneto-resistance change ratio did not change at all up to 10^3 A/cm² while increasing the current density. At 5×10^3 A/cm², the resistance value stayed almost unchanged and the magneto-

resistance change ratio decreased only by about 10%. The signal output voltage of the TMR head according to the fifth and the sixth embodiments was about 1 mV with a current density of 10^3 A/cm² and about 3 mV with a current density of 5×10^3 A/cm². When used for a reproduction magnetic head, the TMR element according to the fifth embodiment can cope with a recording density of 3 Gb/in² or above, and the TMR element according to the sixth embodiment can cope with a recording density of 30 Gb/in² or above.

[Embodiment 7]

Fig. 7 shows a production procedure of a magnetoresistance effect type composite head according to the seventh embodiment. On a wafer substrate made from a composite ceramic of Al₂O₃-TiC constituting a slider, a FeZrN film was formed by sputtering so as to have a thickness of 1 micrometer, which was patterned as the lower shield 101 (Fig. 7A). This FeZrN film was subjected to a thermal treatment at a temperature of 500 degrees C in a vacuum for 1 hour. During this thermal treatment, a uni-directional magnetic field was applied in the horizontal direction in Fig. 7.

Next, a TMR film was formed to constitute the center region by sputtering (Fig. 7B). Firstly, the lower shield 101 was covered with a Ta film 102 with a thickness of 30 nm, a first ferromagnetic layer 103 made

from a Ni-Fe film with a thickness of 10 nm, and a conductive layer of an Al film with a thickness of 2 nm successively formed by sputter deposition in this order. This film formation was carried out using a high-

5 frequency magnetron sputter apparatus having four 4-inch targets. The sputtering condition was set as follows: the background pressure 1×10^{-7} Torr or below, Ar pressure 10 mTorr, high frequency power 200 W. Next, pure oxygen was introduced into the sputter apparatus and

10 the oxygen pressure was maintained in a range from 20 mTorr to 200 Torr for 10 minutes for oxidizing the surface of the Al conductive layer to form the tunnel barrier layer 104. After the oxygen was exhausted to reach the background pressure, a second ferromagnetic

15 layer 105 of a Co-Fe film with a thickness of 20 nm and an antiferromagnetic film of Ni-Mn film with a thickness of 20 nm were formed by way of sputter deposition, thus completing the TMR film.

The TMR film was patterned to form the center

20 region. After this, an insulation film, a permanent magnet film (PM), and a non-magnetic film were formed as an end region to sandwich the center region, and lift-off was carried out (Fig. 7C). An element constituted by the center region and the end region was patterned (Fig. 7

25 D).

Fig. 9 shows a patterning procedure carried out after formation of the TMR film described in the fifth

and the sixth embodiments. The TMR film was formed by the aforementioned method (Fig. 9A); a photo-resist mask 1102 was formed (Fig. 9B); and the patterning was carried out using an ion beam (Fig. 9C).

5 With this photo-resist mask left, sputter deposition was carried out to form a non-magnetic insulation layer 1104 of alumina, a permanent magnet layer 1105 of CoCrPt, and a non-magnetic layer 1106 of Ta (Fig. 9D), and then lift-off was carried out (Fig. 9E). According to this
10 method, the end face of the TMR film patterned is covered with the non-magnetic insulation layer before the permanent magnet layer is formed. Accordingly, no electrical short-circuit is caused between the two magnetic layers facing to each other via the tunnel
15 barrier layer of the TMR film, enabling to maintain a preferable TMR characteristic.

After this, a hole was formed through the insulation film to use a part of the lower shield as an electrode (Fig. 7G). Furthermore, an upper shield of Ni-Fe film
20 was formed with a thickness of 3 micrometers by way of the frame plating method (Fig. 7H).

After this, a magnetic gap was formed from alumina, and a coil for generating a recording magnetic field was formed. This coil was sandwiched by a photo-resist from
25 its top and bottom for insulation. Firstly, a photo-resist pattern serving as the lower insulator was formed on the alumina magnetic gap and thermally hardened at 260

degrees C for 1 hour. Next, the frame plating method was used to form a Cu coil, and a photo-resist pattern serving as the upper insulator was formed. This photo-resist pattern was also thermally hardened at 260 degrees C for 1 hour. Furthermore, a Ni-Fe film with a thickness of 4 micrometers was formed by way of the frame plating method so as to constitute an upper magnetic pole for the recording function. After formation of this upper magnetic pole, a magnetic field of 1 kOe was applied in the direction of the axis of easy magnetization of the magnetic shield, and a thermal treatment was carried out at 200 degrees C for 1 hour. This stabilized the magnetic anisotropy of the upper magnetic pole.

Next, an electrode pattern was formed for the reproduction block and the recording block before the entire element was protected by an alumina sputter film. After this, in order align the magnetization of the antiferromagnetic layer and the adjacent ferromagnetic layer, a uni-directional magnetic field of 3 kOe was applied in the vertical direction to the ABS surface while thermal treatment was carried out at 250 degrees C for 1 hour.

The formation of the TMR film can also be carried out using the conventional method shown in Fig. 12. In this Fig. 12, the undercoat layer 10 is formed from Ta, and the first ferromagnetic layer 11 is formed from Ni-Fe (Fig. 12A). After this, oxygen is introduced into a

vacuum to form an oxidized layer 21 on the surface of the first ferromagnetic layer 11 (Fig. 12B). In the next step, the Al film 12 is formed as a conductive layer, during which oxygen is diffused from the first

5 ferromagnetic layer 11 into the conductive layer 12, thus obtaining an oxidized layer 23 at the side of the conductive layer 12 (Fig. 12C). After formation of the conductive layer 12, the vacuum is maintained while pure oxygen is introduced, so that on the surface of the

10 conductive layer 12 oxidized naturally, a tunnel barrier layer 24 is formed in combination with the layer oxidized by the oxygen diffusion from the rear side (Fig. 12D). In this method, the oxidized layer 24 of the conductive layer 12 is formed on the both boundaries with the

15 ferromagnetic layer. This enables to obtain an element having a further thermally stable characteristic. After the oxygen is exhausted, the second ferromagnetic layer 14 is formed from Co-Fe (Fig. 12E), and the antiferromagnetic layer 15 is formed from Ni-Mn , thus

20 completing the basic configuration of the MR element (Fig. 12F). The TMR film thus obtained exhibits characteristics similar to the TMR film obtained according to the fourth embodiment.

The element thus obtained was cut off from the

25 wafers and processed into a slider configuration for a magnetic disc and mounted on a arm having a gimbal spring for evaluation of recording/reproduction characteristics.

The elements exhibited similar results as those obtained by the fifth and the sixth embodiments

[Overall Evaluation]

5 In the Embodiments 1 to 7, the first ferromagnetic layer was made from a Ni-Fe film, but the first ferromagnetic layer is not to be limited to the Co-Fe film. The first ferromagnetic layer may also be made from Fe, Co, Ni, or an alloy containing these elements,
10 so as to obtain similar results.

Moreover, the antiferromagnetic film is not to be limited to Ni-Mn but may also be made from an alloy containing as a main content Mn-X (X represents at least one element selected from a group consisting of Cr, Fe,
15 Co, Ni, Tc, Ru, Rh, Pd, Re, Os, Ir, and Pt) that enables to obtain similar results.

Moreover, the undercoat film of the TMR film is not to be limited to Ta but may also contain as a main content at least one element selected from a group
20 consisting of Ti, V, Cr, Mn, Fe, Co, Ni, Cu, Zr, Nb, Mo, Tc, Ru, Rh, Pd, Hf, Ta, W, Re, Os, Ir, and Si. These elements also enable to obtain similar results.

Moreover, the magnetic shield is not to be limited to CoTaZr but may also be made from a soft magnetic alloy
25 containing as a main content Fe, Co Ni; or an amorphous soft magnetic alloy containing as a main content Co-M (M represents at least one element selected from a group

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consisting of Ti, V, Cr, Fe, Ni, Cu, Zr, Nb, Mo, Tc, Ru, Rh, Pd, Hf, Ta, W, Re, Os, Ir, Pt, Si, and Al); or a soft magnetic alloy containing as a main content T-A-B (T represents at least one element selected from a group consisting of Fe, Co, Ni; A represents at least one element selected from a group consisting of Ti, V, Cr, Cu, Zr, Nb, Mo, Tc, Ru, Rh, Pd, Hf, Ta, W, Re, Os, Ir, Pt, Si and Al; and B represents at least one element selected from a group consisting of B, N, and O); or a soft

10 magnetic alloy containing as a main content Fe-Si-Al.

These elements enable to obtain similar results.

Thus, the present invention enables to provide a magneto-resistance effect composite head comprising a TMR film element having a preferable resistance value as a head material that can preferably be used for a high-density magnetic recording and reproduction.

The invention may be embodied in other specific forms without departing from the spirit or essential characteristic thereof. The present embodiments are therefore to be considered in all respects as illustrative and not restrictive, the scope of the invention being indicated by the appended claims rather than by the foregoing description and all changes which come within the meaning and range of equivalency of the claims are therefore intended to be embraced therein.

The entire disclosure of Japanese Patent Application No. 09-335501 (Filed on December 5th, 1997)

including specification, claims, drawings and summary are incorporated herein by reference in its entirety.

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WHAT IS CLAIMED IS:

1. A magneto-resistance effect type composite head comprising:

a first magnetic shield and a second magnetic shield successively layered on a slider;

5 a reproduction head including a magneto-resistance effect element (hereinafter, referred to as an MR element) arranged between said first and said second magnetic shields; and

10 a recording head arranged adjacent to said reproduction head so as to use said second magnetic shield as a first magnetic pole film and having a second magnetic pole film opposing to said first magnetic pole via a magnetic gap;

said MR element comprising:

15 a center region including a ferromagnetic tunnel junction magneto-resistance effect film (hereinafter, referred to as a TMR film) having: a first ferromagnetic layer and a second ferromagnetic layer for generating a magneto-resistance effect using said first and said
20 second magnetic shields as electrodes so that a current flows in a an almost vertical direction between said first and said second magnetic shields; and a tunnel barrier layer provided between said first and said second ferromagnetic layer; and

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25 an end region arranged to sandwich said center region from both sides for applying a bias magnetic field to said center region.

2. A magneto-resistance effect type composite head as claimed in Claim 1, wherein said TMR film includes an undercoat layer, said first ferromagnetic layer, said tunnel barrier layer, said second ferromagnetic layer, 5 and an antiferromagnetic layer successively formed in this order.

3. A magneto-resistance effect type composite head as claimed in Claim 1, wherein said TMR film includes an undercoat layer, an antiferromagnetic layer, said first ferromagnetic layer, said tunnel barrier layer, said 5 second ferromagnetic layer, and a non-magnetic conductive layer successively formed in this order.

4. A magneto-resistance effect type composite head as claimed in Claim 2, wherein said antiferromagnetic film is made from an alloy containing as a main content Mn-X, wherein X represents at least one element selected 5 from a group consisting of Cr, Fe, Co, Ni, Tc, Ru, Rh, Pd, Re, Os, Ir, and Pt.

5. A magneto-resistance effect type composite head as claimed in Claim 3, wherein said antiferromagnetic film is made from an alloy containing as a main content Mn-X, wherein X represents at least one element selected 5 from a group consisting of Cr, Fe, Co, Ni, Tc, Ru, Rh, Pd, Re, Os, Ir, and Pt.

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6. A magneto-resistance effect type composite head as claimed in Claim 2, wherein said undercoat layer contains as a main content at least one element selected from a group consisting of Ti, V, Cr, Mn, Fe, Co, Ni, Cu, Zr, Nb, Mo, Tc, Ru, Rh, Pd, Hf, Ta, W, Re, Os, Ir, Pt, and Si

7. A magneto-resistance effect type composite head as claimed in Claim 3, wherein said undercoat layer contains as a main content at least one element selected from a group consisting of Ti, V, Cr, Mn, Fe, Co, Ni, Cu, Zr, Nb, Mo, Tc, Ru, Rh, Pd, Hf, Ta, W, Re, Os, Ir, Pt, and Si.

8. A magneto-resistance effect type composite head as claimed in Claim 1, wherein said first and said second ferromagnetic layers are formed from Fe, Co, or Ni, or an alloy containing Fe, Co, or Ni.

9. A magneto-resistance effect type composite head as claimed in Claim 2, wherein said first and said second ferromagnetic layers are formed from Fe, Co, or Ni, or an alloy containing Fe, Co, or Ni.

10. A magneto-resistance effect type composite head as claimed in Claim 3, wherein said first and said second ferromagnetic layers are formed from Fe, Co, or Ni, or an alloy containing Fe, Co, or Ni.

11. A magneto-resistance effect type composite head as claimed in Claim 1, wherein said magnetic shields are

made from a soft magnetic alloy containing as a main content Fe, Co, or Ni.

12. A magneto-resistance effect type composite head as claimed in Claim 1, wherein said magnetic shields are made from an amorphous soft magnetic alloy containing as a main content Co-M, wherein M represents at least one element selected from a group consisting of Ti, V, Cr, Fe, Ni, Cu, Zr, Nb, Mo, Tc, Ru, Rh, Pd, Hf, Ta, W, Re, Os, Ir, Pt, Si, and Al.

13. A magneto-resistance effect type composite head as claimed in Claim 1, wherein said magnetic shields are made from a soft magnetic alloy containing as a main content T-A-B, wherein T represents at least one element selected from a group consisting of Fe, Co, and Ni; A represents at least one element selected from a group consisting of Ti, V, Cr, Cu, Zr, Nb, Mo, Ru, Rh, Pd, Hf, Ta, W, Re, Os, Ir, Pt, Si, and Al; and B represents at least one element selected from a group consisting of C, N, and O.

14. A magneto-resistance effect type composite head as claimed in Claim 1, wherein said magnetic shields are made from a soft magnetic alloy containing as a main content Fe-Si-Al.

15. A magneto-resistance effect type composite head as claimed in Claim 1, wherein an electrically connected area between said TMR film and said second magnetic

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shield is equal to or smaller than an area of said TMR

5 film opposing to said second magnetic shield.

16. A magneto-resistance effect type composite head as claimed in Claim 1, wherein an insulator is provided on a junction surface between said center region and said end region.

17. A magneto-resistance effect type composite head as claimed in Claim 1, wherein said end region includes a non-magnetic insulation film, a permanent magnet film, and a non-magnetic film successively arranged in this

5 order.

18. A magneto-resistance effect composite head
production method comprising steps of:

forming a first magnetic shield on a slider;

forming a ferromagnetic tunnel junction magneto-
resistance effect (hereinafter, referred to as TMR)
element having a center region constituted by a TMR film
and an end region for applying a bias magnetic field to
said TMR film; and

forming a second magnetic shield;

10 said TMR element forming step including steps of:
forming said TMR film, forming a photo-resist mask on
said TMR film, patterning said TMR film by said photo-
resist mask, and lifting-off said end region by said
photo-resist mask.

19. A magneto-resistance effect type composite head
production method as claimed in Claim 18, said method

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ABSTRACT OF THE DISCLOSURE

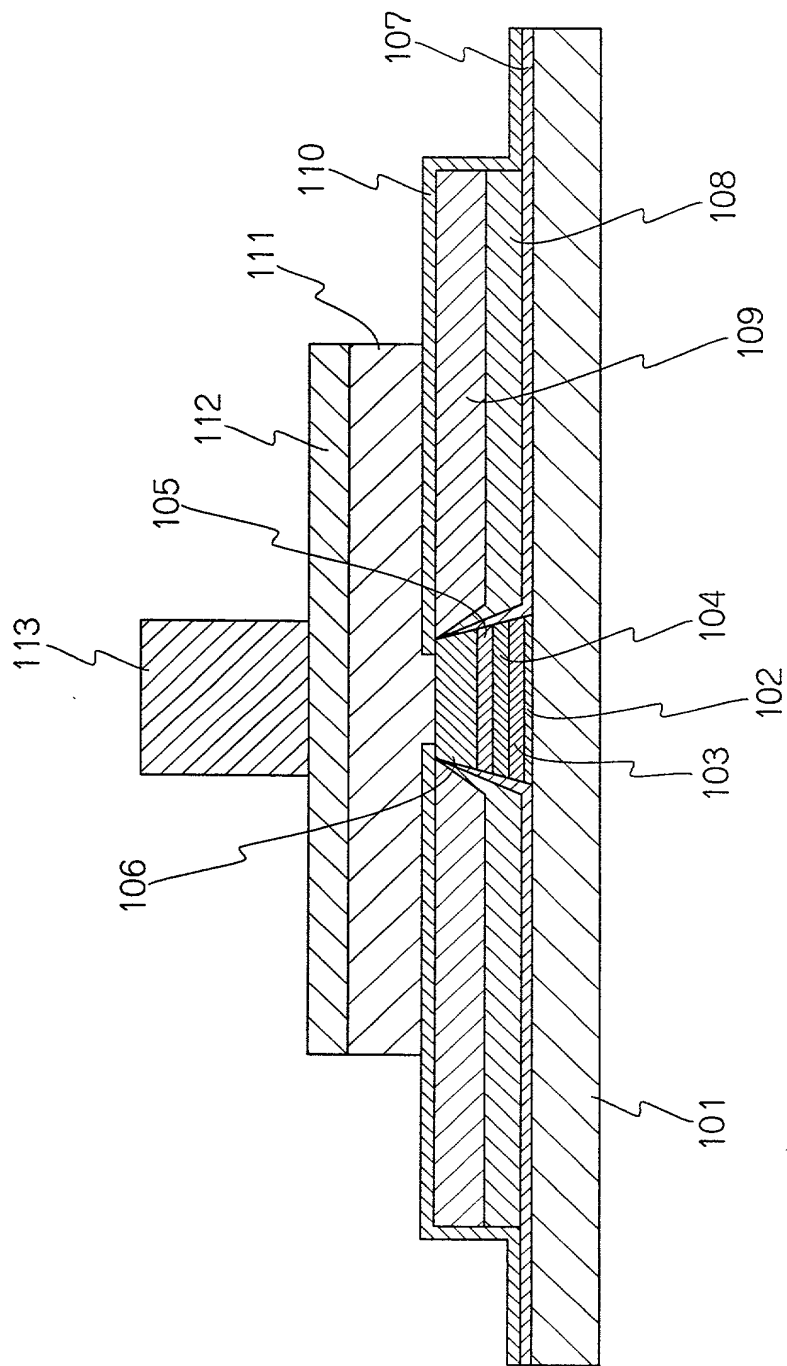
The present invention provides a magneto-resistance effect (hereinafter, referred to as MR) type composite head comprising: a reproduction head including an MR
5 element arranged between a first and a second magnetic shield; and a recording head arranged adjacent to the reproduction head so as to use the second magnetic shield as a first magnetic pole film and having a second
10 magnetic pole film opposing to the first magnetic pole via a magnetic gap;

the MR element comprising:

a center region including a ferromagnetic tunnel
junction magneto-resistance effect film (hereinafter,
referred to as a TMR film) having: a first ferromagnetic
15 layer and a second ferromagnetic layer for generating a magneto-resistance effect using the first and the second magnetic shields as electrodes so that a current flows in an almost vertical direction between the first and the second magnetic shields; and a tunnel barrier layer
20 provided between the first and the second ferromagnetic layer; and

an end region arranged to sandwich the center region from both sides for applying a bias magnetic field to the center region.

FIG.1



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FIG. 2

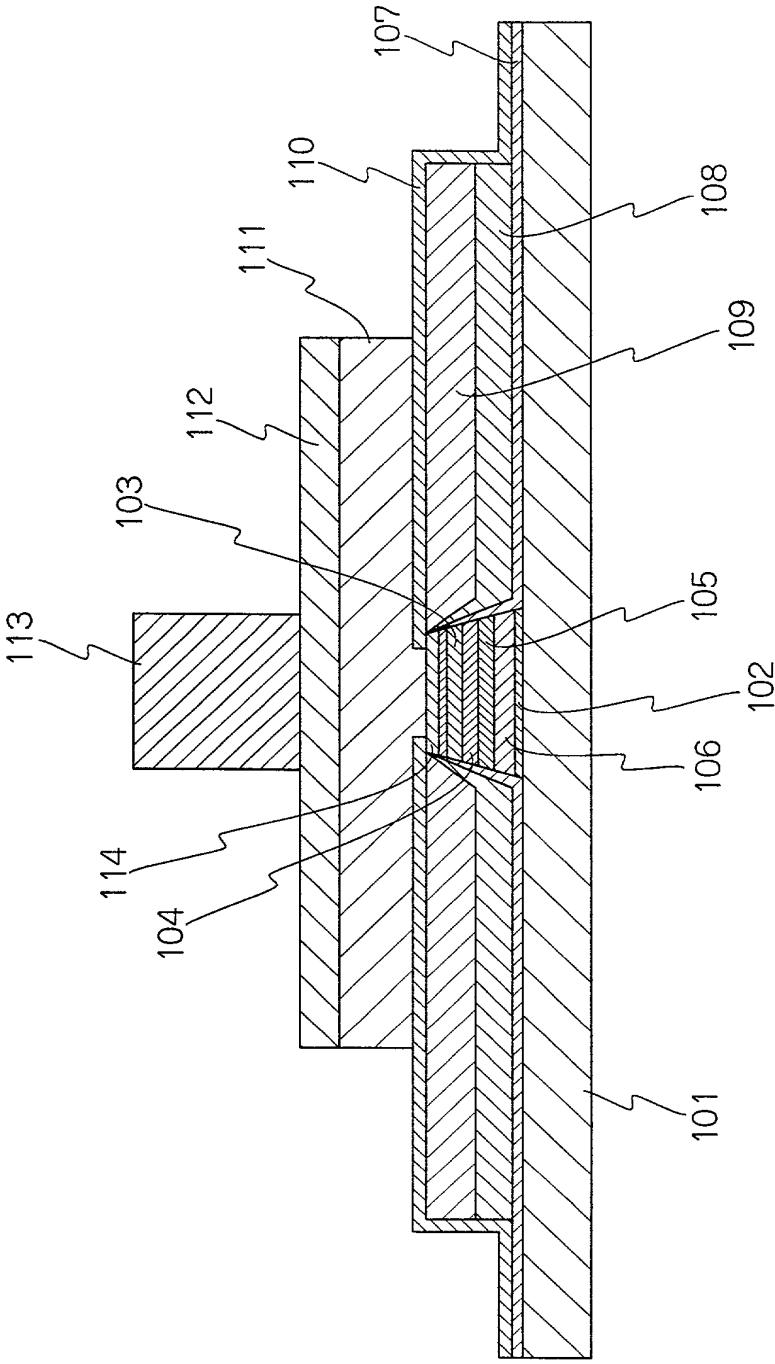
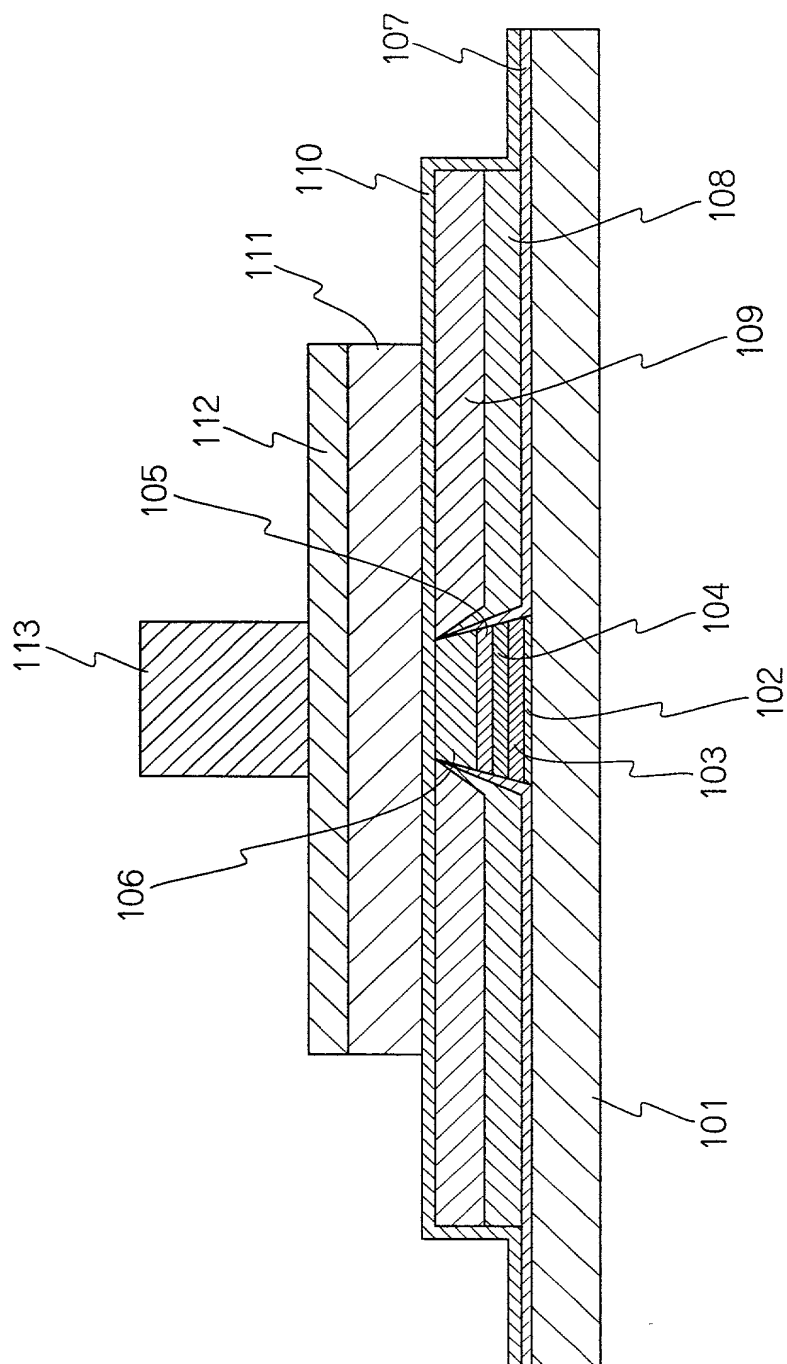


FIG. 3



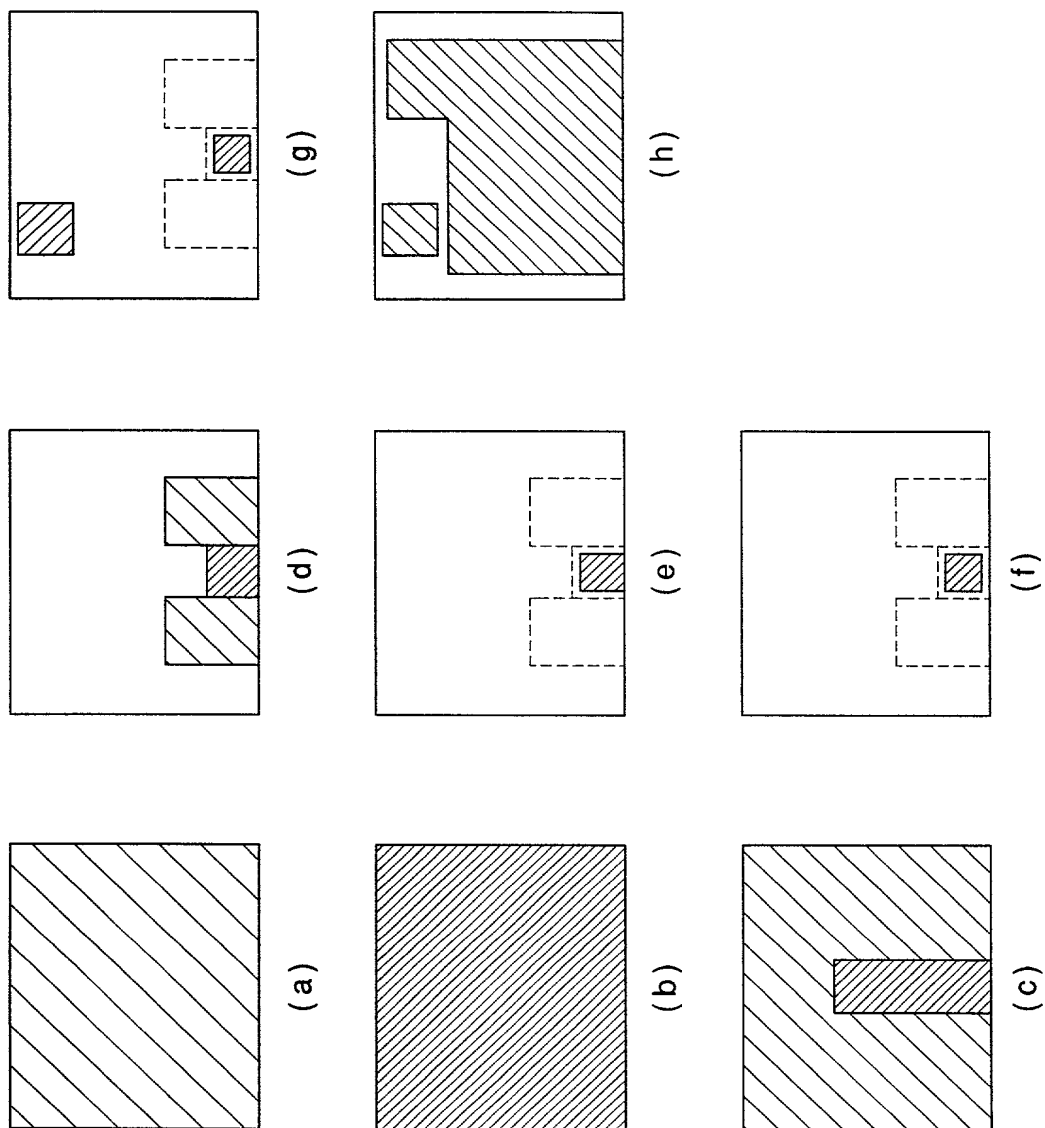


FIG. 5

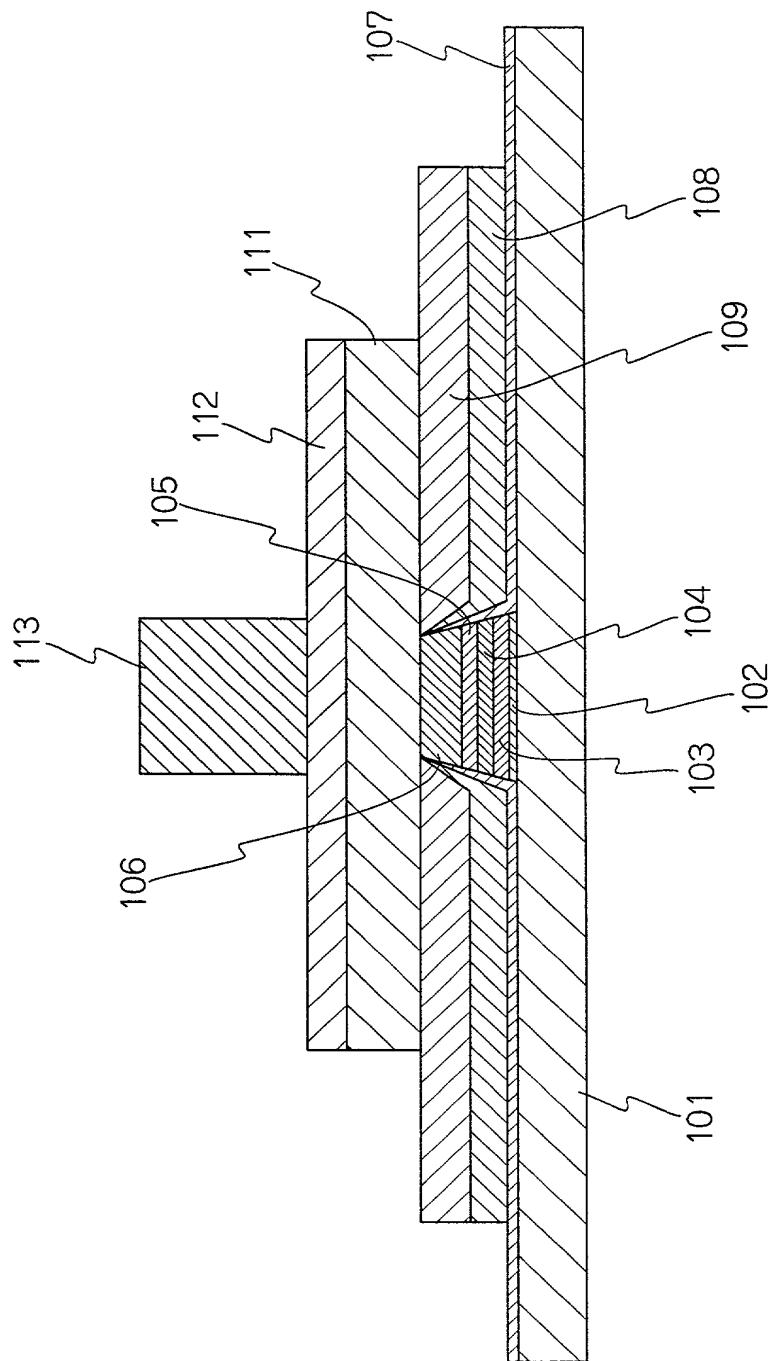


FIG. 6

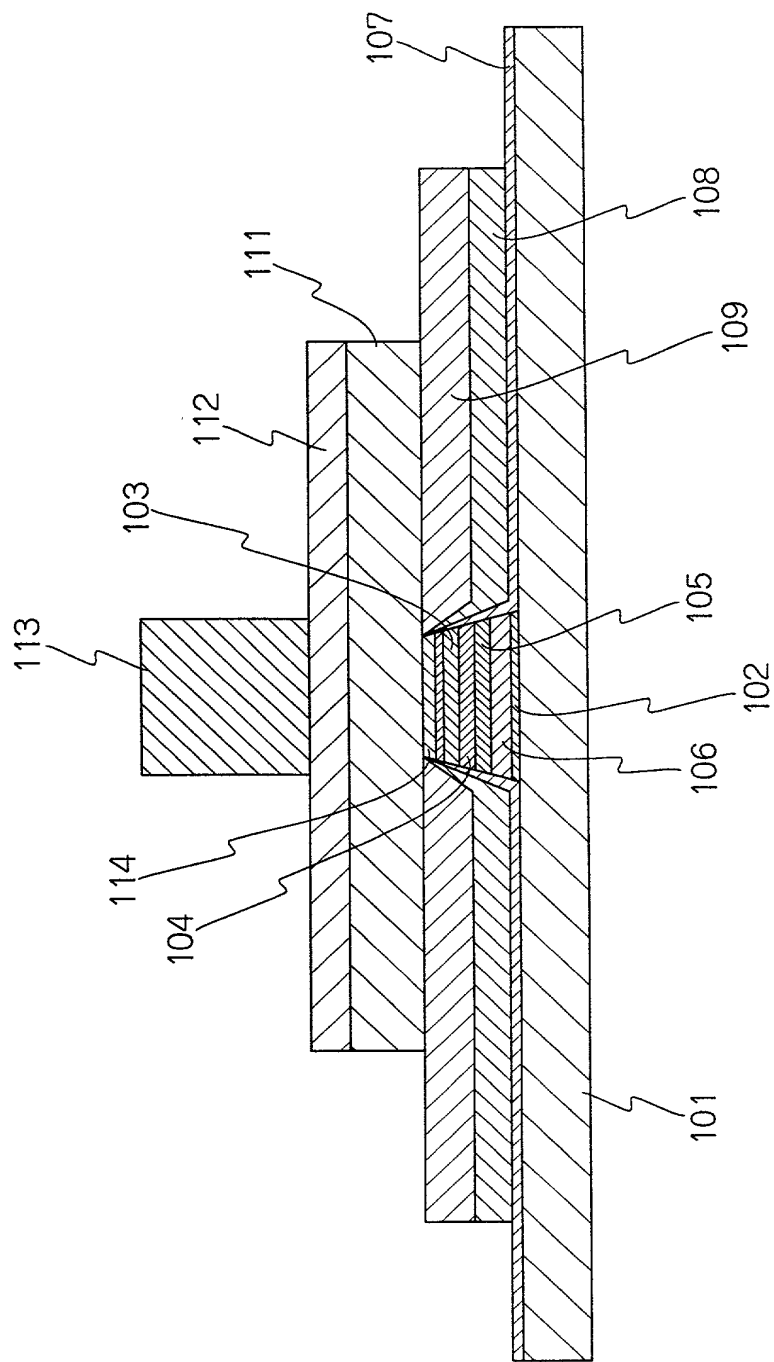


FIG. 7

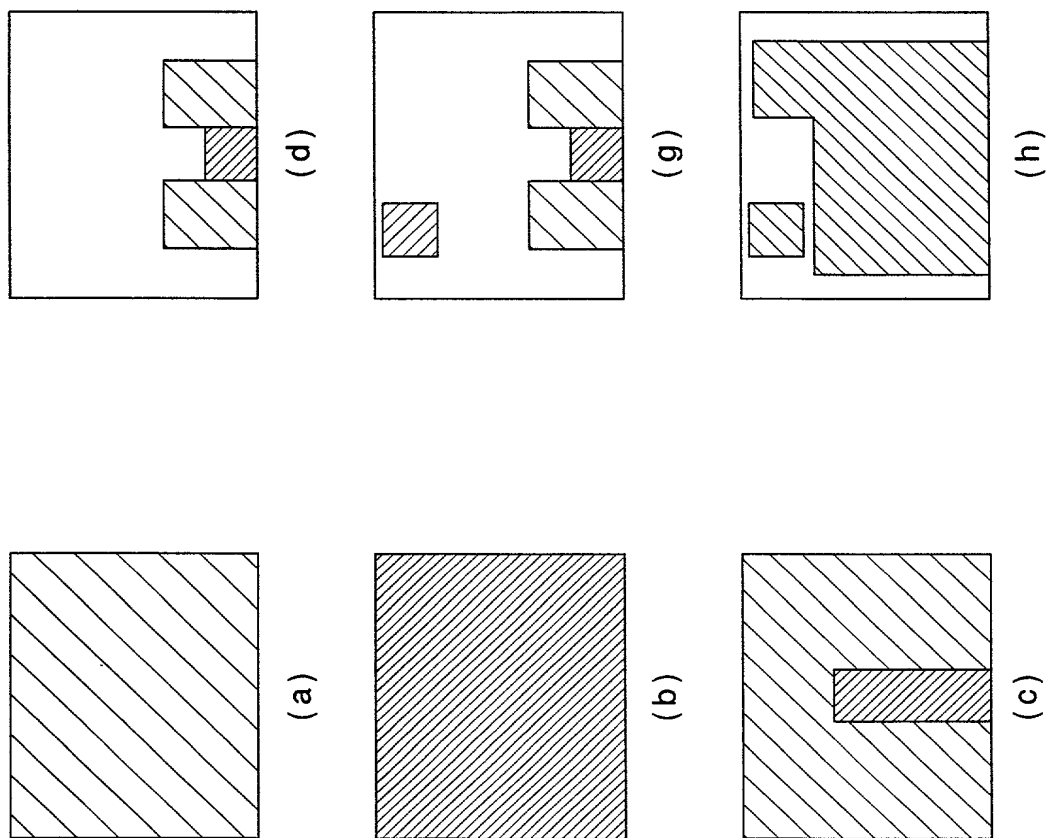


FIG. 8

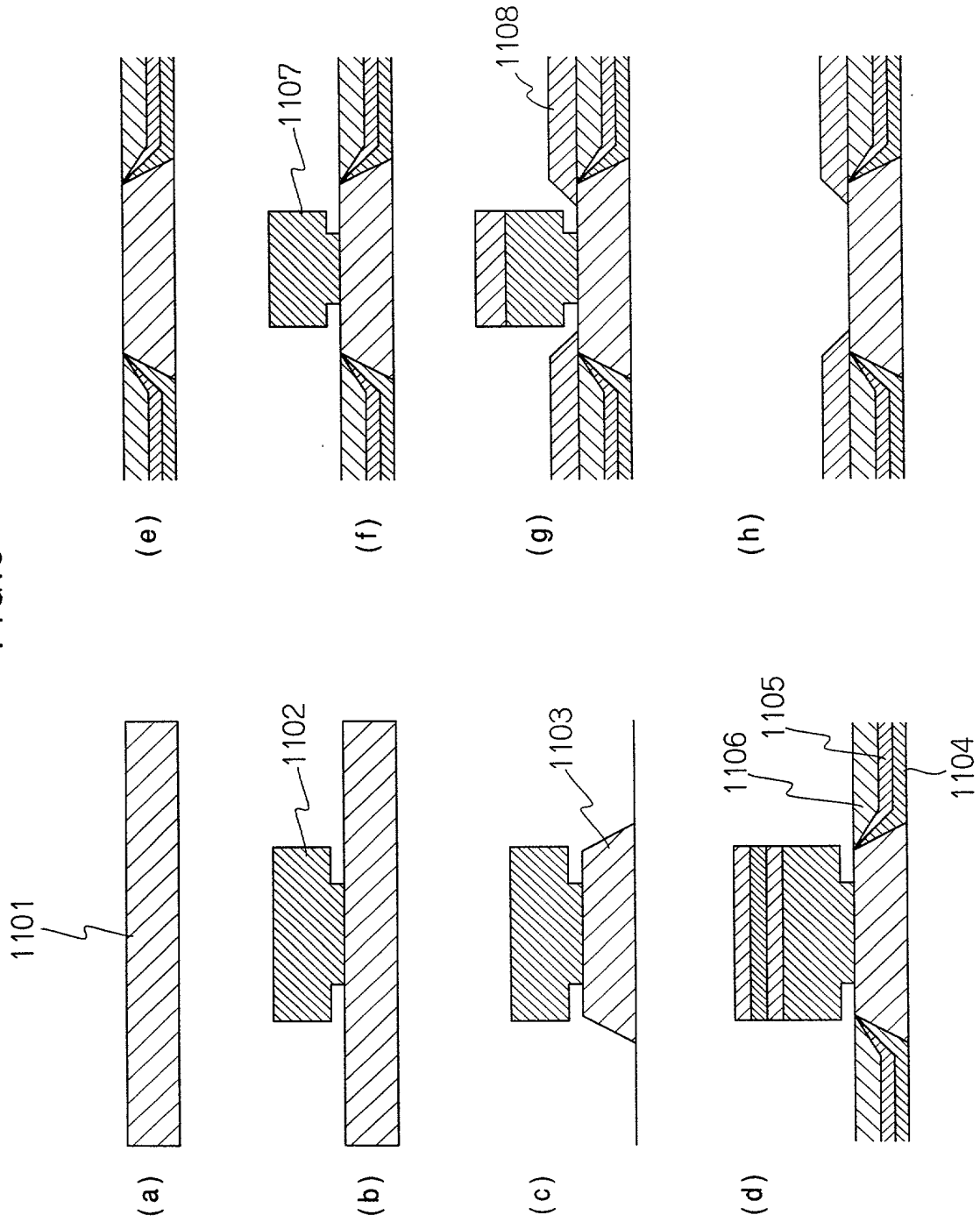


FIG. 9

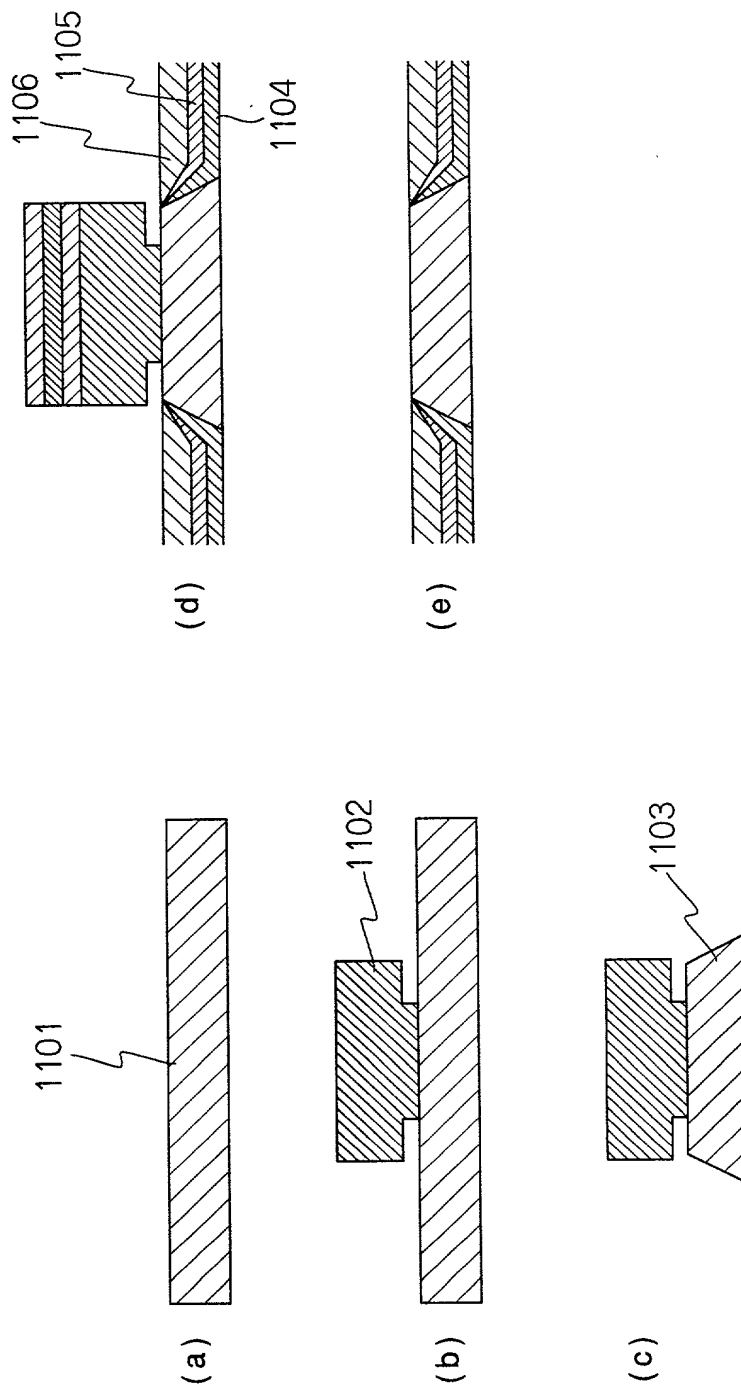


FIG.10

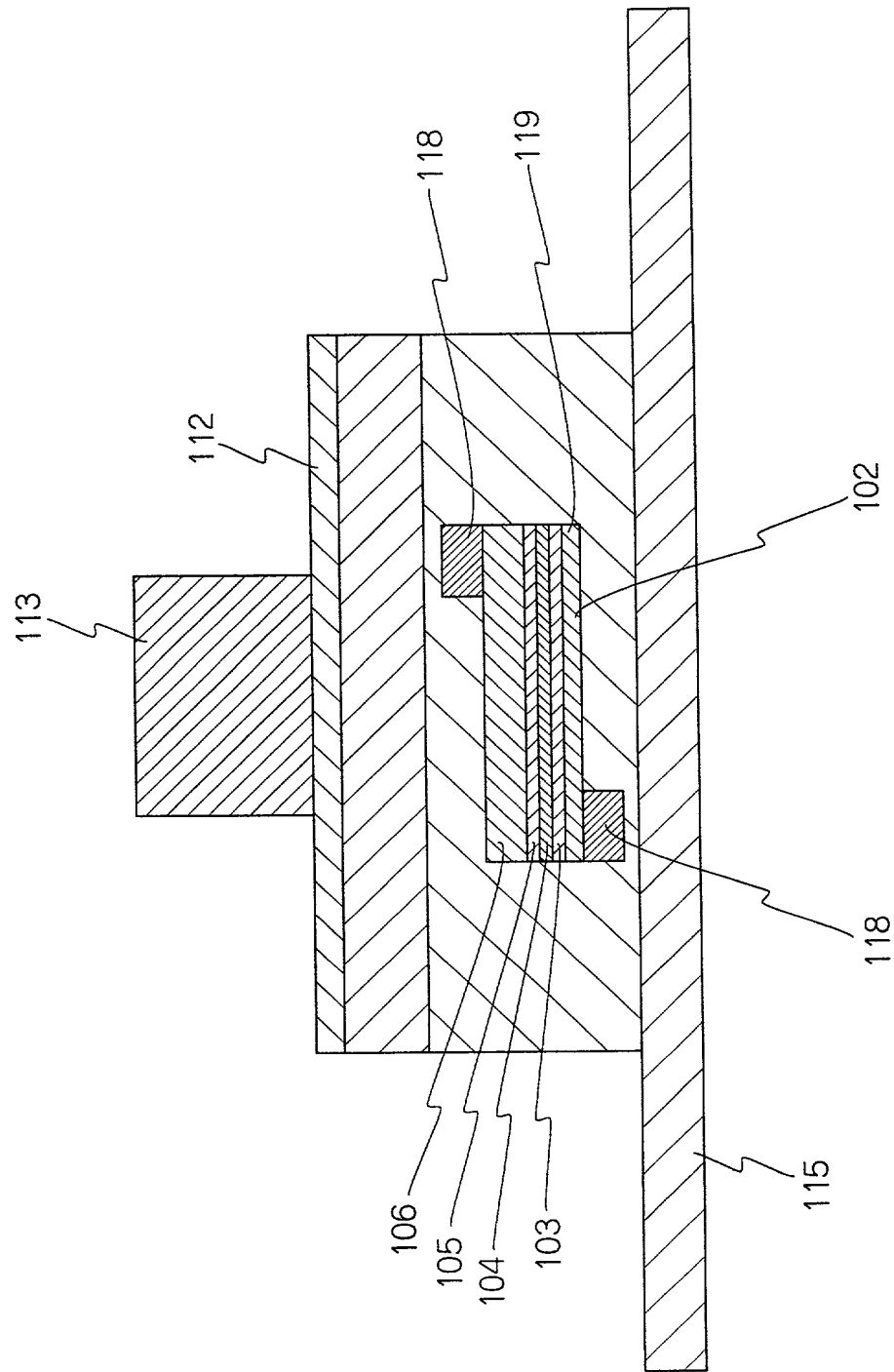


FIG. 11

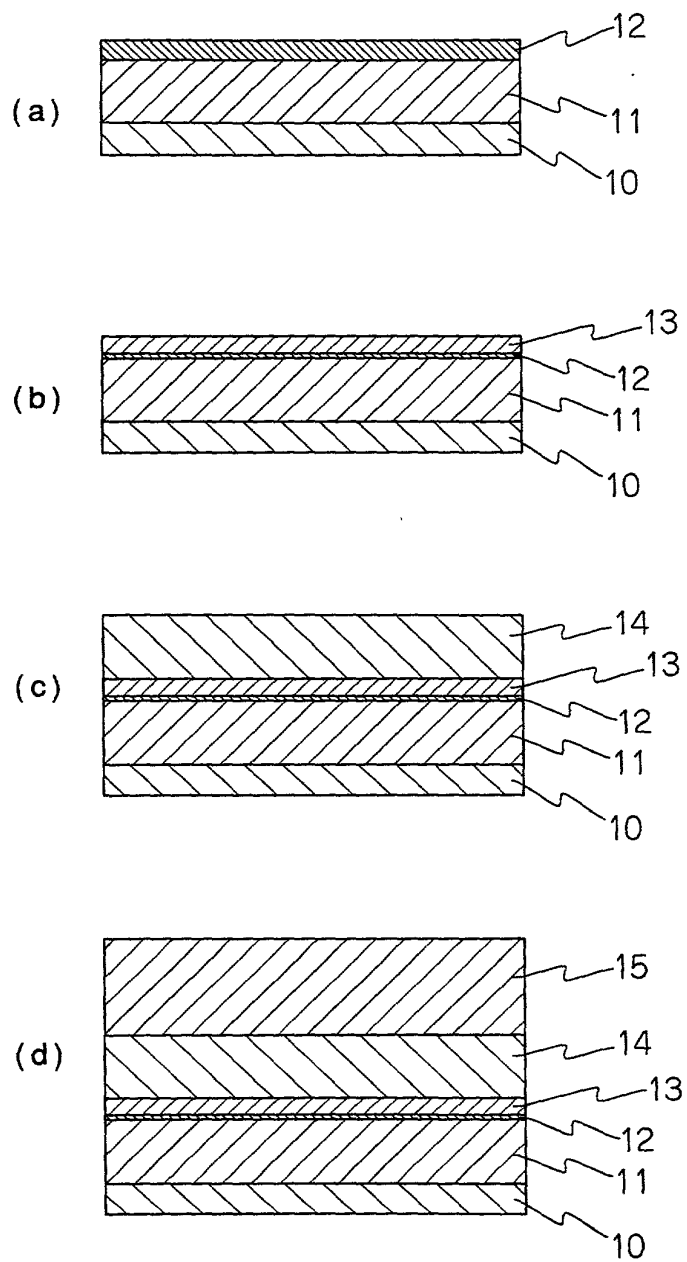
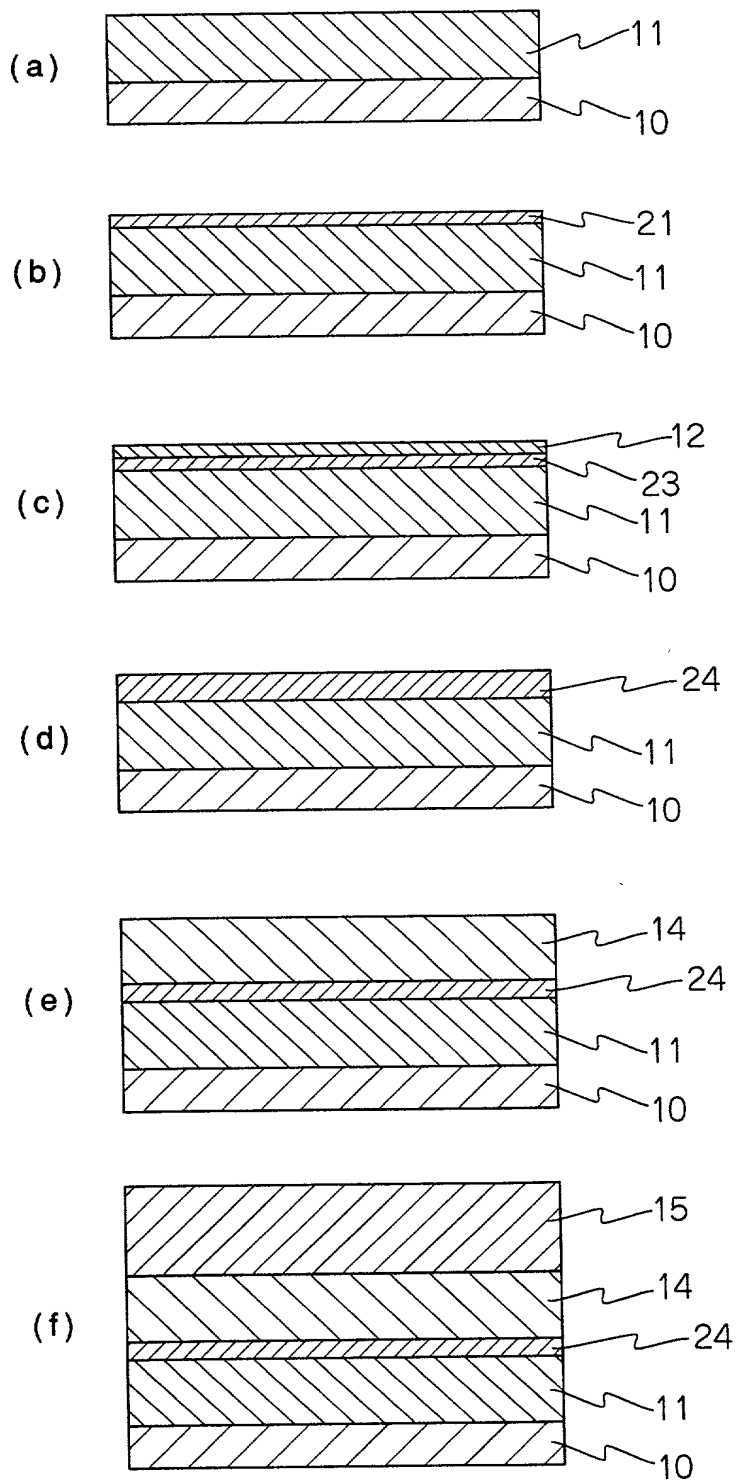


FIG.12



Declaration and Power of Attorney For Patent Application

English Language Declaration

As a below named inventor, I hereby declare that:

My residence, post office address and citizenship are as stated below next to my name,

I believe I am the original, first and sole inventor (if only one name is listed below) or an original, first and joint inventor (if plural names are listed below) of the subject matter which is claimed and for which a patent is sought on the invention entitled
MAGNETO-RESISTANCE EFFECT TYPE COMPOSITE HEAD AND PRODUCTION METHOD THEREOF

the specification of which

(check one)

☐ is attached hereto.

☐ was filed on _____ as

Application Serial No. _____

and was amended on _____
 (if applicable)

I hereby state that I have reviewed and understand the contents of the above identified specification, including the claims, as amended by any amendment referred to above.

I acknowledge the duty to disclose information which is material to patentability as defined in Title 37, Code of Federal Regulations § 1.56.

I hereby claim foreign priority benefits under Title 35, United States Code, §119 of any foreign application(s) for patent or inventor's certificate listed below and have also identified below any foreign application for patent or inventor's certificate having a filing date before that of the application on which priority is claimed:

Prior Foreign Application(s)			Priority Claimed	
<u>9-335501</u>	<u>Japan</u>	<u>05/12/1997</u>	<input checked="" type="checkbox"/>	<input type="checkbox"/>
(Number)	(Country)	(Day/Month/Year Filed)	Yes	No
<u> </u>	<u> </u>	<u> </u>	<input type="checkbox"/>	<input type="checkbox"/>
(Number)	(Country)	(Day/Month/Year Filed)	Yes	No
<u> </u>	<u> </u>	<u> </u>	<input type="checkbox"/>	<input type="checkbox"/>
(Number)	(Country)	(Day/Month/Year Filed)	Yes	No

I hereby claim the benefit under Title 35, United States Code, §120 of any United States application(s) listed below and, insofar as the subject matter of each of the claims of this application is not disclosed in the prior United States application in the manner provided by the first paragraph of Title 35, United States Code, § 112, I acknowledge the duty to disclose information which is material to patentability as defined in Title 37, Code of Federal Regulations, § 1.56 which became available between the filing date of the prior application and the national or PCT international filing date of this application:

(Application Serial No.)

(Filing Date)

(Status)
(patented, pending, abandoned)

(Application Serial No.)

(Filing Date)

(Status)
(patented, pending, abandoned)

I hereby declare that all statements made herein of my own knowledge are true and that all statements made on information and belief are believed to be true; and further that these statements were made with the knowledge that willful false statements and the like so made are punishable by fine or imprisonment, or both, under Section 1001 of Title 18 of the United States Code and that such willful false statements may jeopardize the validity of the application or any patent issued thereon.

POWER OF ATTORNEY: As a named inventor, I hereby appoint the following attorney(s) and/or agent(s) to prosecute this application and transact all business in the Patent and Trademark Office connected therewith. *(list name and registration number)*

ROBERT J. PATCH, REG. NO. 17,355; ANDREW J. PATCH, REG. NO. 32,925;

ROBERT F. HARGEST, REG. NO. 25,590; BENOIT CASTEL, REG. NO. 35,041

Send Correspondence to: YOUNG & THOMPSON, SUITE 200,
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Direct Telephone Calls to: *(name and telephone number)* ROBERT PATCH, 703/521-2297

Full name of sole or first inventor Ishiwata Nobuyuki	
Inventor's signature <i>Ishiwata Nobuyuki</i>	Date 20/11/1998
Residence Tokyo, Japan	
Citizenship Japanese	
Post Office Address c/o NEC Corporation, 7-1, Shiba 5-chome, Minato-ku, Tokyo, Japan	
Full name of second joint inventor, if any Hisanao Tsuge	
Second inventor's signature <i>Hisanao Tsuge</i>	Date 20/11/1998
Residence Tokyo, Japan	
Citizenship Japanese	
Post Office Address c/o NEC Corporation, 7-1, Shiba 5-chome, Minato-ku, Tokyo, Japan	

(Supply similar information and signature for third and subsequent joint inventors.)

(Application Serial No.)	(Filing Date)	(Status) (patented, pending, abandoned)
(Application Serial No.)	(Filing Date)	(Status) (patented, pending, abandoned)

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ROBERT F. HARGEST, REG. NO. 25,590; BENOIT CASTEL, REG. NO. 35,041

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Full name of ^{third} inventor Hisao Matsutera	
Inventor's signature <i>Hisao Matsutera</i>	Date 20/11/1998
Residence Tokyo, Japan	
Citizenship Japanese	
Post Office Address c/o NEC Corporation, 7-1, Shiba 5-chome, Minato-ku, Tokyo, Japan	
Full name of ^{fourth} joint inventor, if any Yuji Tsukamoto	
Second inventor's signature <i>Yuji Tsukamoto</i>	Date 20/11/1998
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Citizenship Japanese	
Post Office Address c/o NEC Corporation, 7-1, Shiba 5-chome, Minato-ku, Tokyo, Japan	

(Supply similar information and signature for third and subsequent joint inventors.)

(Application Serial No.)

(Filing Date)

(Status)
(patented, pending, abandoned)

(Application Serial No.)

(Filing Date)

(Status)
(patented, pending, abandoned)

I hereby declare that all statements made herein of my own knowledge are true and that all statements made on information and belief are believed to be true; and further that these statements were made with the knowledge that willful false statements and the like so made are punishable by fine or imprisonment, or both, under Section 1001 of Title 18 of the United States Code and that such willful false statements may jeopardize the validity of the application or any patent issued thereon.



POWER OF ATTORNEY: As a named inventor, I hereby appoint the following attorney(s) and/or agent(s) to prosecute this application and transact all business in the Patent and Trademark Office connected therewith. (list name and registration number)

ROBERT J. PATCH, REG. NO. 17,355; ANDREW J. PATCH, REG. NO. 32,925;

ROBERT F. HARGEST, REG. NO. 25,590; BENOIT CASTEL, REG. NO. 35,041

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Full name of <u>fifth</u> inventor	
Masafumi Nakada	
Inventor's signature	Date
<i>Masafumi Nakada</i> 	20/11/1998
Residence	
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Citizenship	
Japanese	
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Full name of <u>sixth</u> joint inventor, if any	
Atsushi Kamijo	
Second inventor's signature	Date
<i>Atsushi Kamijo</i> 	20/11/1998
Residence	
Tokyo, Japan	
Citizenship	
Japanese	
Post Office Address	
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(Supply similar information and signature for third and subsequent joint inventors.)